

TIP41A TIP42A

COMPLEMENTARY SILICON POWER TRANSISTOR

Features

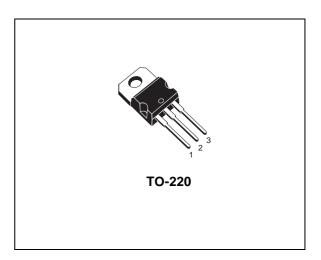
- COMPLEMENTARY PNP-NPN DEVICES
- NEW ENHANCED SERIES
- HIGH SWITCHING SPEED
- h_{FE} IMPROVED LINEARITY

Applications

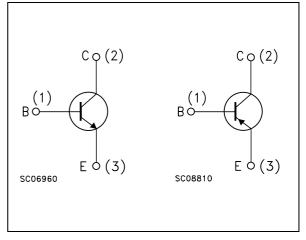
- GENERAL PURPOSE CIRCUITS
- AUDIO AMPLIFIER
- POWER LINEAR AND SWITCHING

Description

The TIP41A is a silicon base island technology NPN power transistor Jedec TO-220 plastic package with improved performances than the industry standard TIP41A that make this device suitable for audio, power linear and switching applications. The complementary PNP type is TIP42A.



Internal Schematic Diagram



Order Codes

Part Number	Marking	Package	Packing
TIP41A	TIP41A	TO-220	TUBE
TIP42A	TIP42A	TO-220	TUBE

1 Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage ($I_E = 0$)	60	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	60	V
V_{EBO}	Emitte-Base Voltage (I _C = 0)	5	V
I _C Collector Current		6	A
I _{CM}	Collector Peak Current	10	А
Ι _Β	Base Current	3	mA
P	Total dissipation at T _{case} = 25°C	65	W
P _{TOT}	T _{amb} = 25°C	2	W
T _{stg}	Storage Temperature	-65 to 150	°C
ТJ	Max. Operating Junction Temperature	150	°C

Table 1.	Absolute	Maximum	Ratings
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Note: For PNP types voltage and current values are negative

2 Electrical Characteristics

 $T_{case} = 25^{\circ}C$; unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 30 V			0.7	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5V			1	mA
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 60V			0.4	mA
V _{CEO(sus)} Note: 1	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30mA	60			V
V _{CE(sat)} Note: 1	Collector-Emitter saturation Voltage	I _C = 6A I _B = 0.6A			1.5	V
V _{BE(on)} Note: 1	Base-Emitter Voltage	$I_{C} = 6A$ $V_{CE} = 4V$			2	V
h _{FE}	DC Current Gain	$I_{C} = 0.3A$ $V_{CE} = 4V$				
Note: 1		$I_{C} = 3A$ $V_{CE} = 4V$	15		75	
h _{fe}	Small Signal Current Gain	$\begin{split} I_{C} &= 0.5A \ V_{CE} = 10V \ f=1 \ \text{KHz} \\ I_{C} &= 0.5A \ V_{CE} = 10V \ f=1 \ \text{KHz} \end{split}$	20 3			

Table 2. Electrical Characteristics

Note: 1 Pulsed duration = $300 \ \mu s$, duty cycle $\leq 1.5\%$.

For PNP types voltage e current values are negative.



DG14600

68 1_C (A)

 $V_{CE} = 1V$

T_I =150 °C

2.1 Typical Characteristic

Figure 1. DC Current Gain (NPN)



T_J = 25 °C

*

 $T_J = -40^{\circ}C$

⁸10^{-1²}

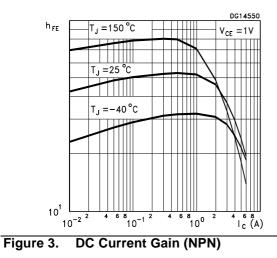
⁴ ⁶ ⁸ 10⁰

h _{FE}

10²

10¹

10⁻²



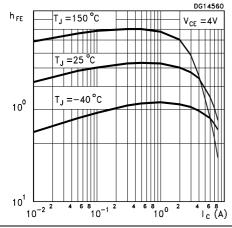


Figure 4. DC Current Gain (PNP)

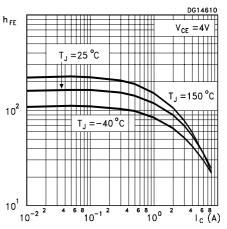
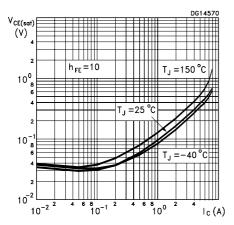
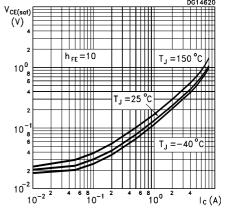


Figure 5. Collector-Emitter Saturation Voltage Figure 6. Collector-Emitter Saturation Voltage (NPN) (PNP)



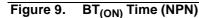
PNP)





V_{BE(sat)} (V) $h_{FE} = 10$ 1.2 $T_J = -40 \degree C$ 1.1 T_J = 25 °C 1.0 0.9 0.8 0.7 0.6 T_J =150 °C 0.5 0.4 0.3 ⁸10⁻¹ ⁸10⁰ 10⁻² I_C (A)

Figure 7. Base-Emitter Saturation Voltage (NPN)



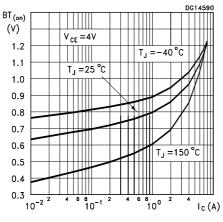


Figure 11. Resistive Load Switching Time (NPN)

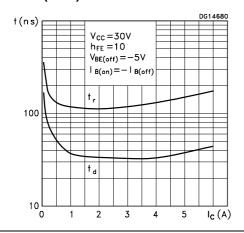
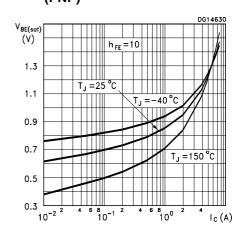
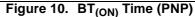


Figure 8. Base-Emitter Saturation Voltage (PNP)





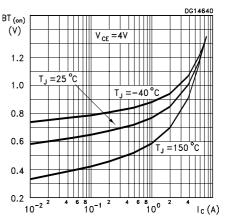
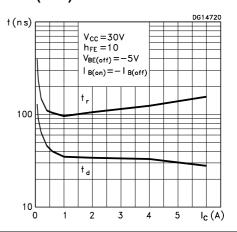
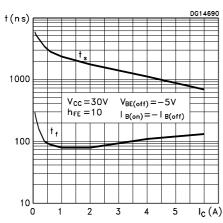
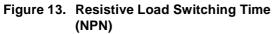


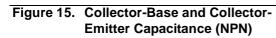
Figure 12. Resistive Load Switching Time (PNP)



57







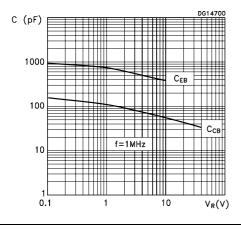


Figure 14. Resistive Load Switching Time (PNP)

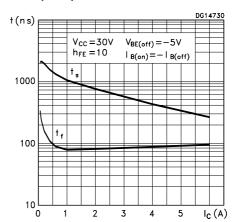
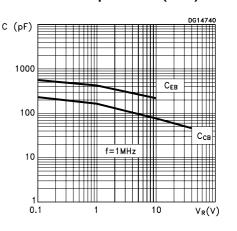


Figure 16. Collector-Base and Collector-Emitter Capacitance (PNP)



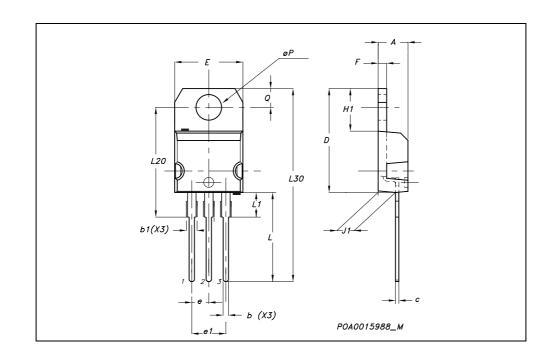
3 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



DIM.		mm.		inch		
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX
А	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

TO-220 MECHANICAL DATA





4 Revision History

Date	Revision	Changes
27-Oct-2005	1	Initial Release



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10/10

